

ULTRA FAST RECOVERY RECTIFIER DIODES

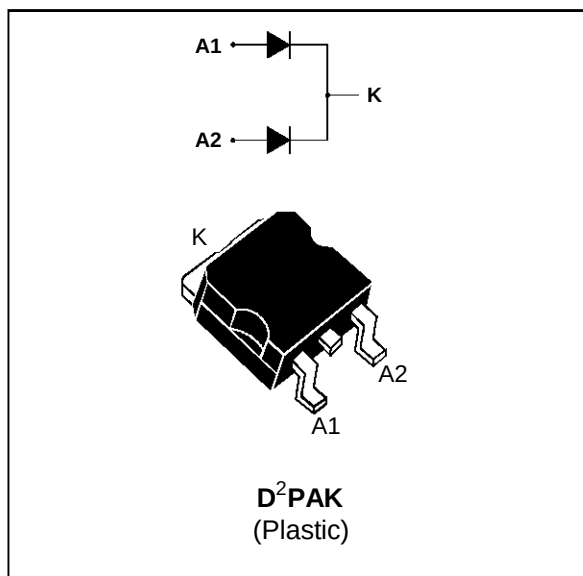
FEATURES

- SUITED FOR SMPS
- LOW LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIME
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- SMD PACKAGE

DESCRIPTION

Low cost dual center tap rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged in D²PAK this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE MAXIMUM (limiting values)

Symbol	Parameter			Value	Unit
$I_{F(RMS)}$	RMS forward current		Per diode	10	A
$I_{F(AV)}$	Average forward current $\delta = 0.5$	$T_c = 125^\circ\text{C}$	Per diode	5	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ms}$ sinusoidal	Per diode	50	A
T_{stg} T_j	Storage and junction temperature range			- 65 to + 150 - 65 to + 150	$^\circ\text{C}$ $^\circ\text{C}$

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	200	V

STPR1020CG

THERMAL RESISTANCE

Symbol	Parameter		Value	Unit
Rth (j-c)	Junction to case	Per diode	4.0	°C/W
		Total		
Rth (c)	Coupling			°C/W

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th}(j-c) (\text{Per diode}) + P(\text{diode 2}) \times R_{th}(c)$$

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	T _j = 25°C	V _R = V _{RRM}			50	μA
	T _j = 100°C				0.5	mA
V _F **	T _j = 125°C	I _F = 5 A			0.99	V
	T _j = 125°C	I _F = 10 A			1.20	
	T _j = 25°C	I _F = 10 A			1.25	

Pulse test : * tp = 5 ms, duty cycle < 2 %

** tp = 380 μs, duty cycle < 2 %

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
trr	T _j = 25°C	I _F = 0.5A I _{rr} = 0.25A I _R = 1A			30	ns
tfr	T _j = 25°C	I _F = 1A tr = 10 ns V _{FR} = 1.1 x V _F		20		ns
V _{FP}	T _j = 25°C	I _F = 1A tr = 10 ns		3		V

To evaluate the conduction losses use the following equation :

$$P = 0.78 \times I_{F(AV)} + 0.042 \times I_{F(RMS)}^2$$

Fig.1 : Average forward power dissipation versus average forward current (Per diode).

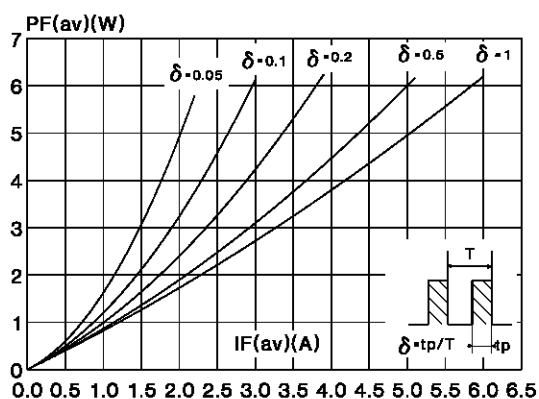


Fig.2 : Peak current versus form factor. (Per diode)

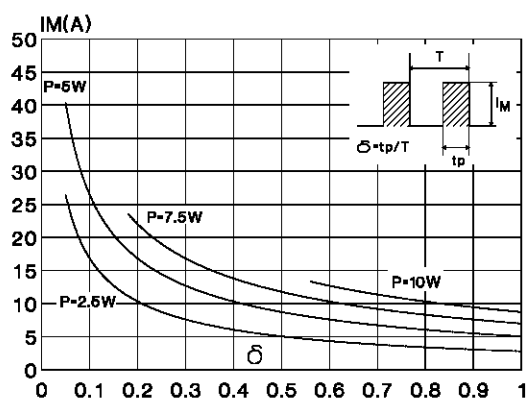


Fig.3 : Average current versus ambient temperature. (duty cycle : 0.5)

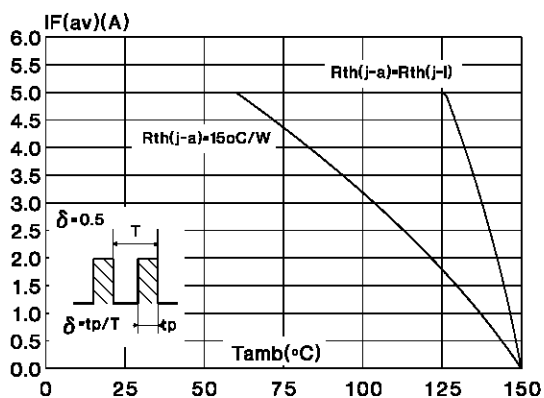


Fig.4 : Non repetitive surge peak forward current versus overload duration (Maximum values) (Per diode).

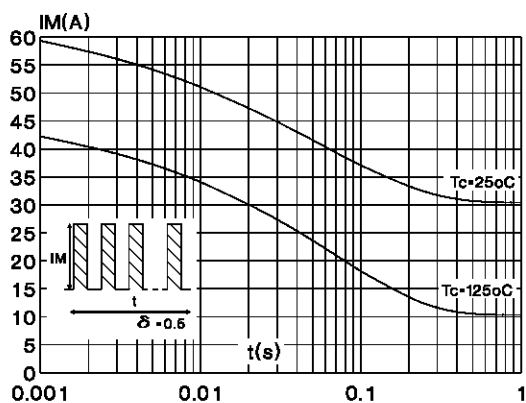


Fig.5 : Relative variation of thermal transient impedance junction to case versus pulse duration. (Per diode).

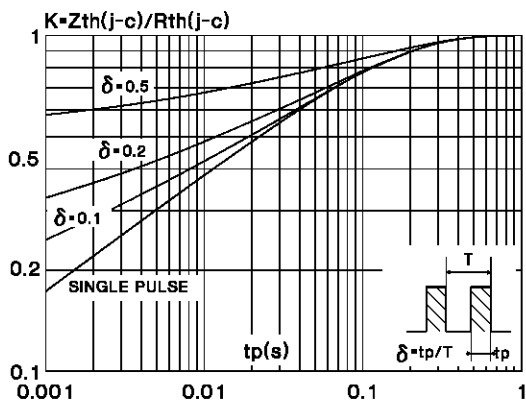


Fig.6 : Forward voltage drop versus forward current. (maximum values) (Per diode).

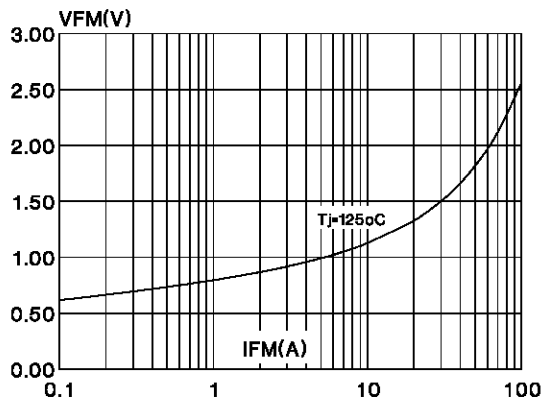


Fig.7 : Junction capacitance versus reverse voltage applied (Typical values) (Per diode).

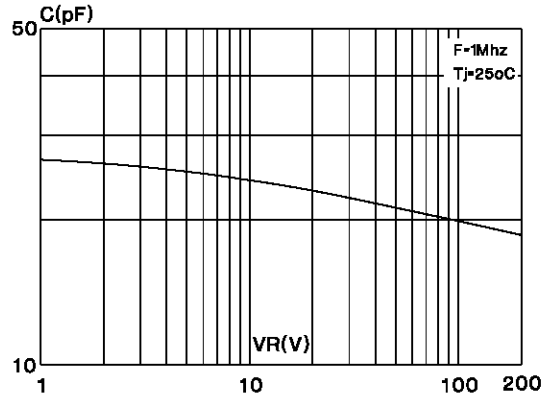


Fig.8 : Recovery charges versus dI_F/dt (Per diode).

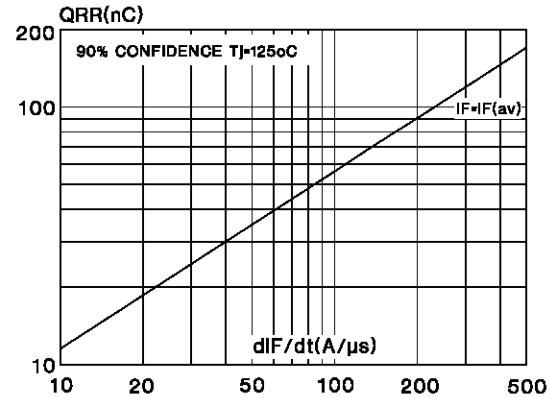


Fig.9 : Peak reverse current versus dI_F/dt (Per diode).

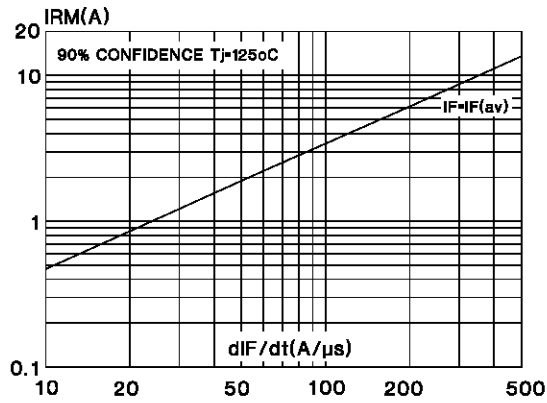
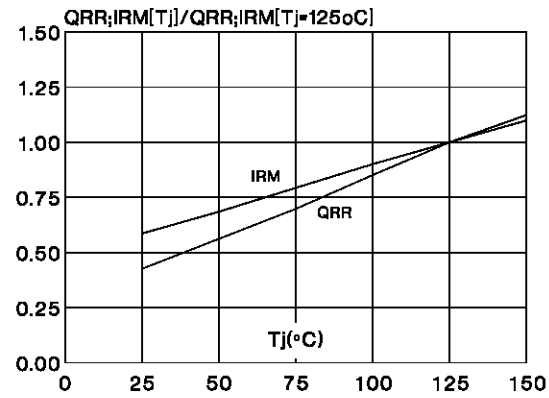


Fig.10 : Dynamic parameters versus junction temperature (Per diode).



PACKAGE MECHANICAL DATAD²PAK (Plastic)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.70		0.93	0.027		0.037
B2	1.25		1.40	0.049		0.055
C	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	9.00		9.35	0.354		0.368
E	10.00		10.28	0.393		0.405
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.37	0.050		0.054
L3	1.40		1.75	0.055		0.069

Cooling method : C
 Marking : Type number
 Weight : 1.8 g

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